RN2Z

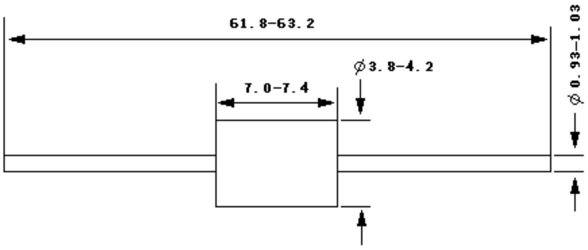
SILICON RECTIFIER DIODE
Forward Current – 2.0 Ampere

Features

- For pulse rectification applications

Mechanical Data

- Case: Resin molded



Dimensions in mm

Absolute Maximum Ratings and Characteristics

	Symbols	Rating	Units
Transient Peak Reverse Voltage	V_{RSM}	200	V
Peak Reverse Voltage	V_{RM}	200	V
Average Forward Current at $T_C = 125\,^{O}C$	$I_{F(AV)}$	2	A
Peak Surge Forward Current 10mS Single Half Sine	I_{FSM}	70	A
Junction Temperature	T_j	-40 to +150	^{O}C
Storage Temperature Range	T_S	-40 to +150	^{O}C

Characteristics (Ta=25 ^{o}C,unless otherwise specified)

	Symbol	Value(max.)	Unit
Forward Voltage Drop at I_F=2A	V_F	0.92	V
Reverse Leakage Current at V_R=V_{RM}	I_R	50	µA
Reverse Leakage Current Under High Temperature at V_R=V_{RM},, T_j=150^{o}C	HI_R	4	mA
Reverse Recovery Time, Recovery point 90% at I_F=I_{RP}=100mA	Trr-1	100	nS
Reverse Recovery Time, Recovery point 75% at I_F=100Ma,I_{RP}=200mA	Trr-2	50	nS
Thermal Resistance Between Junction and Lead	θj-1	12	^{O}C/W